Low Threshold Long Wavelength Interband Cascade Lasers

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Interband cascade lasers (ICLs) [1-2] employ type-II quantum wells (QWs) as the active region and can cover a wide range of mid-IR spectrum with high performance especially in wavelength range from 3 μ m to about 6 μ m [2-4]. In this work, we report significant improvements in long wavelength ICLs in terms of reduced threshold current density J_{th} and voltage V_{th} compared to previous ICLs [5]. For example, in cw operation, the J_{th} at 80 K is below 9 A/cm² with output power exceeding 100 mW/facet and with a lasing wavelength near 10.7 μ m close to 140 K as shown in Fig.1. Such a low J_{th} indicates a weak SRH recombination, suggesting a good material quality. The threshold voltage V_{th} at 80K is 3.61 V with a voltage efficiency of 73%, which is quite high considering that the photon energy (126meV) is low at such a long wavelength (9.83 μ m at 80 K). ICLs from another wafer EB7910 lased at a longer wavelength in cw mode near 11.4 μ m at 80 K with a J_{th} of 24.9 A/cm² and V_{th} of 3.95 V, corresponding a voltage efficiency of about 55%. These ICLs were able to operate at wavelengths exceeding 12 μ m in pulsed mode at 135 K as shown in Fig. 2, the longest ever reported for ICLs with standard W-shape QW active regions. Detailed results will be presented at the conference.



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